



# The effect of synthetic rubbers on the electrical properties of graphene

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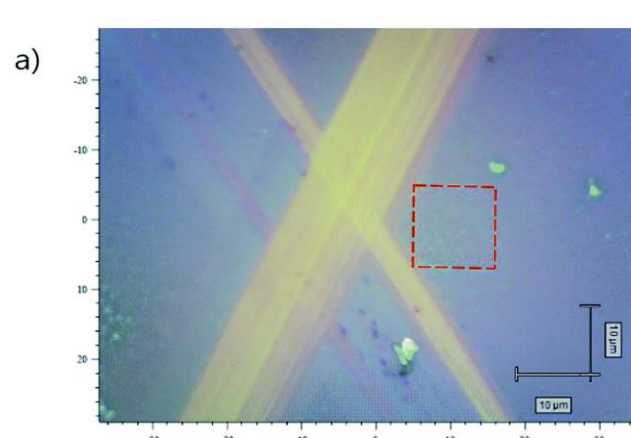
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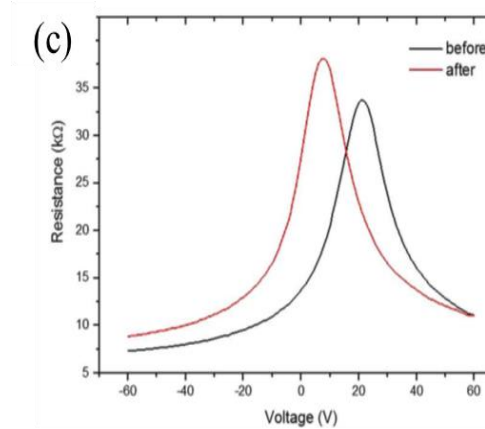
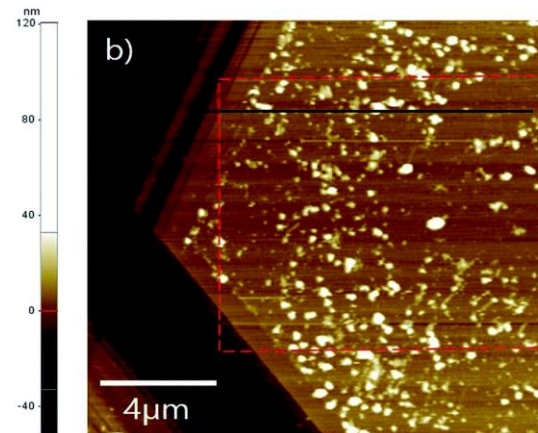
## Problems with CVD graphene

- Graphene is a promising candidate to be used as a filler material for rubber in tires. Graphene can fill the gaps in between rubber molecules to make it more stronger.
- The main issue with CVD graphene is the PMMA residues attached to the graphene during transfer and lithography process.

Graphene on Si/SiO<sub>2</sub>



AFM image of Graphene on Si/SiO<sub>2</sub>



**Table 1** Cleaning results of electronic properties for four different FET devices

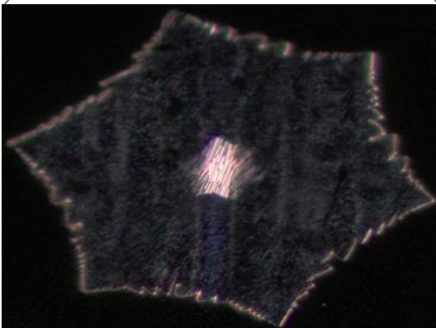
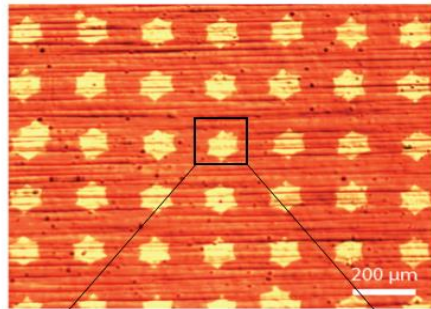
Sample name	Electron mobility (cm <sup>2</sup> V <sup>-1</sup> s <sup>-1</sup> )		Hole mobility (cm <sup>2</sup> V <sup>-1</sup> s <sup>-1</sup> )		Dirac point shift (V)	
	Before	After	Before	After	Before	After
A	788.2	842.5	631.5	702.0	+33.0	+22.1
B	789.9	835.3	645.8	617.9	+21.6	+8.4
C	2047.1	2257.5	1440.9	1500.3	+24.2	+7.9
D	716.0	849.3	619.8	630.3	+22.3	+7.6

Choi W, Shehzad M A, Park S and Seo Y 2017 Influence of removing PMMA residues on surface of CVD graphene using a contact-mode atomic force microscope *RSC Adv.* **7** 6943–9

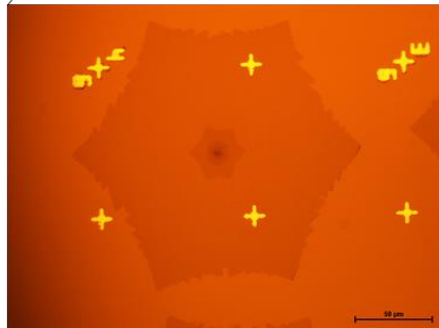
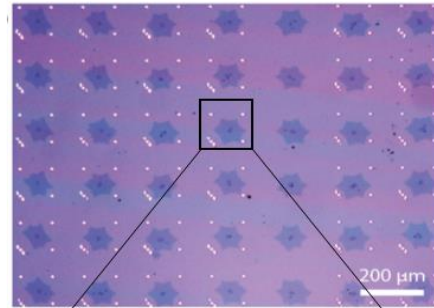
# Project - 1

## Two-step PMMA removal from CVD graphene used during transfer and lithography process towards high quality graphene

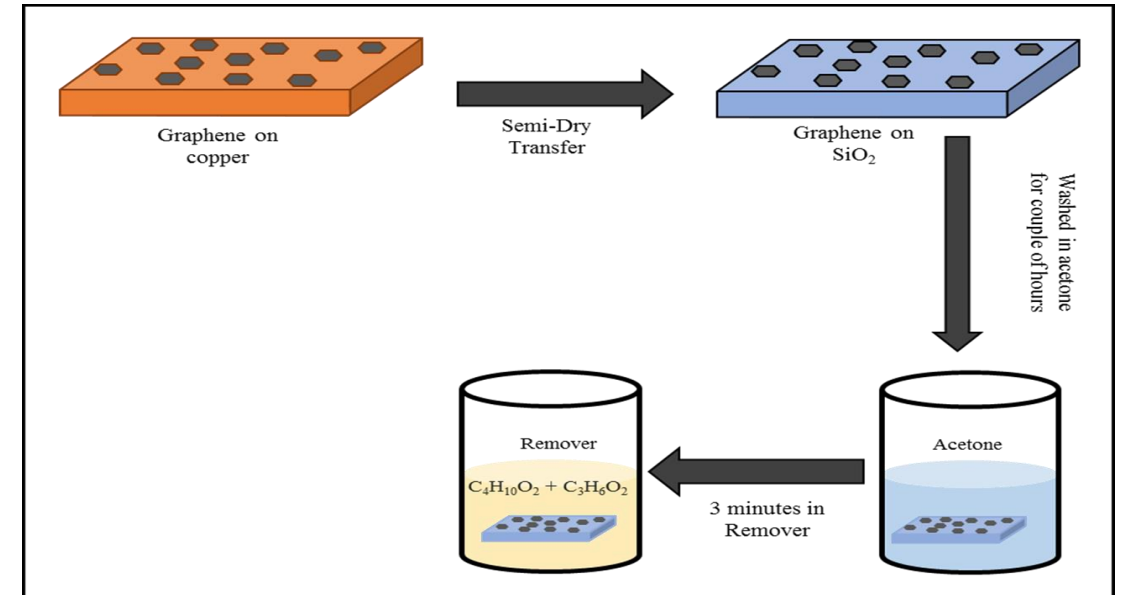
(a) Graphene on Cu



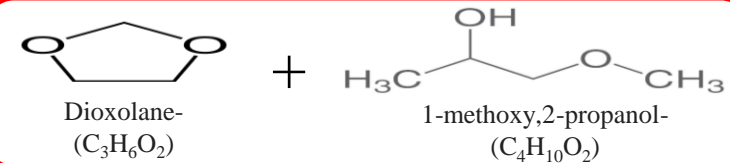
(b) Graphene on Si/SiO<sub>2</sub>



Miseikis V, Bianco F, David J, Gemmi M, Pellegrini V, Romagnoli M and Coletti C 2017 Deterministic patterned growth of high-mobility large-crystal graphene: A path towards wafer scale integration *2D Mater.* **4**



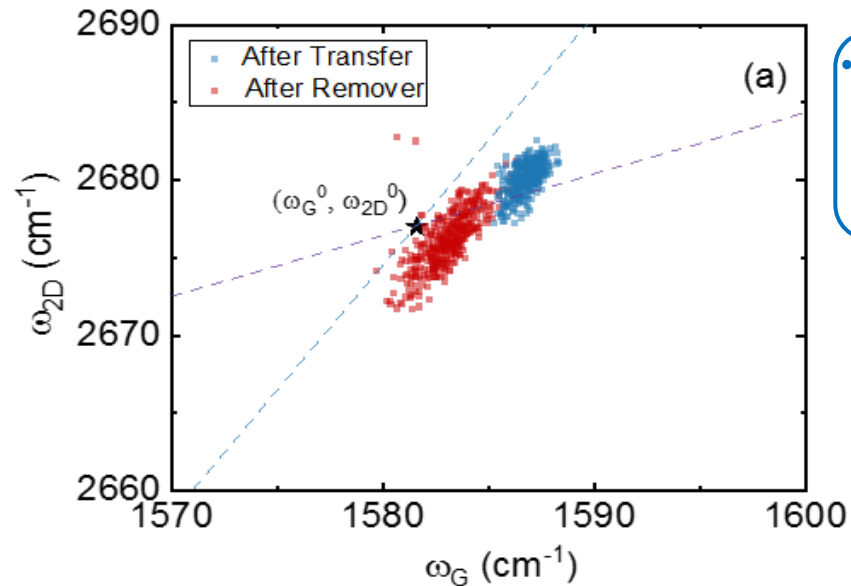
Schematic cleaning procedure of CVD graphene.



Remover-(AR-600-71)

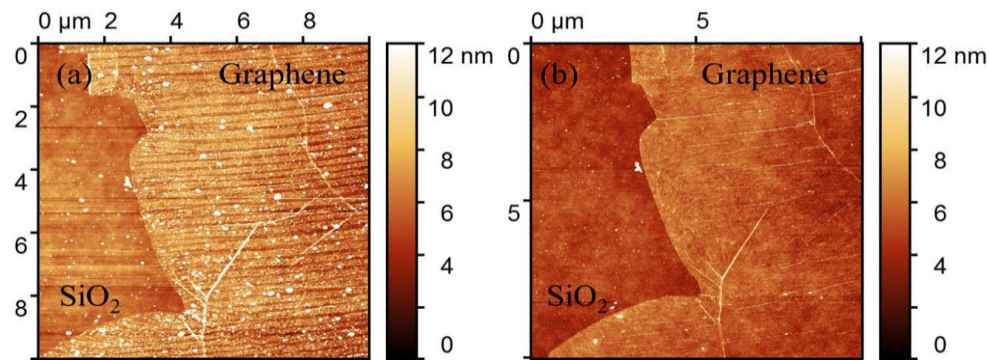
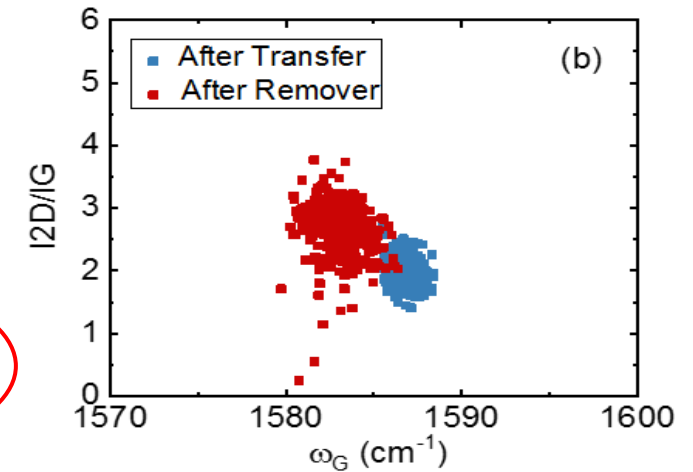
Tyagi et al in preparation.

## Raman and AFM results after transfer and cleaning with remover

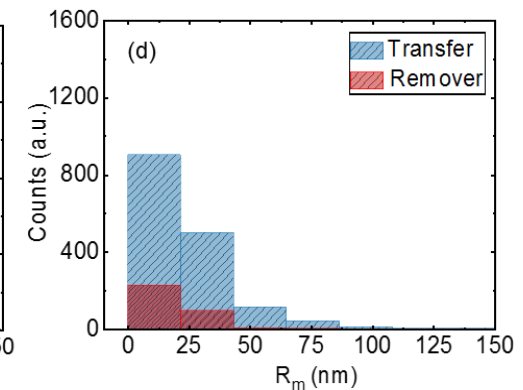
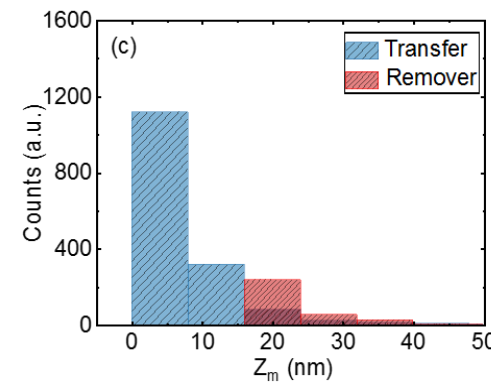


- Strain and doping effect decoupling by using Raman correlation between 2D and G peak positions.

- Intensity ratio increment confirming the doping reduction.



- PMMA residues are detached from the graphene surface by using remover which were left after conventional acetone treatment.



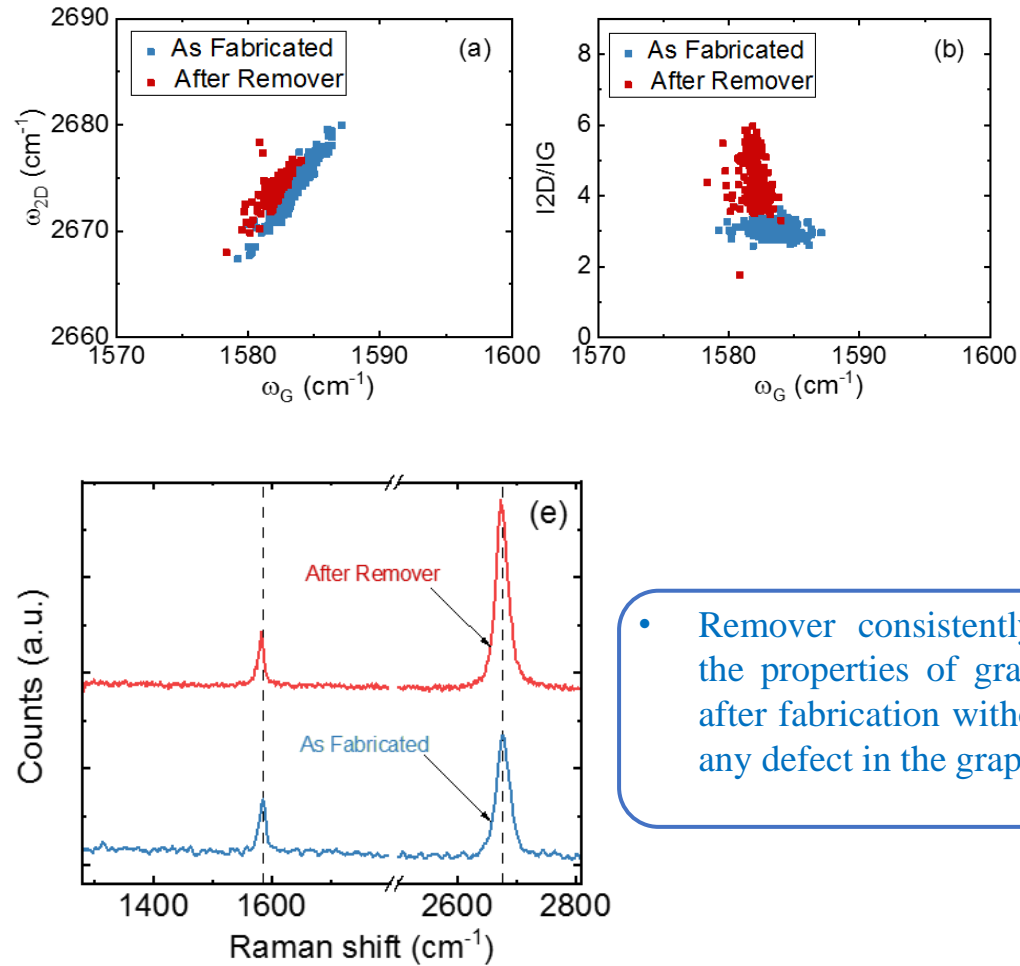
- Height and size of the PMMA residues calculated using the AFM data which is in agreement with Raman results.

Tyagi et al in preparation.

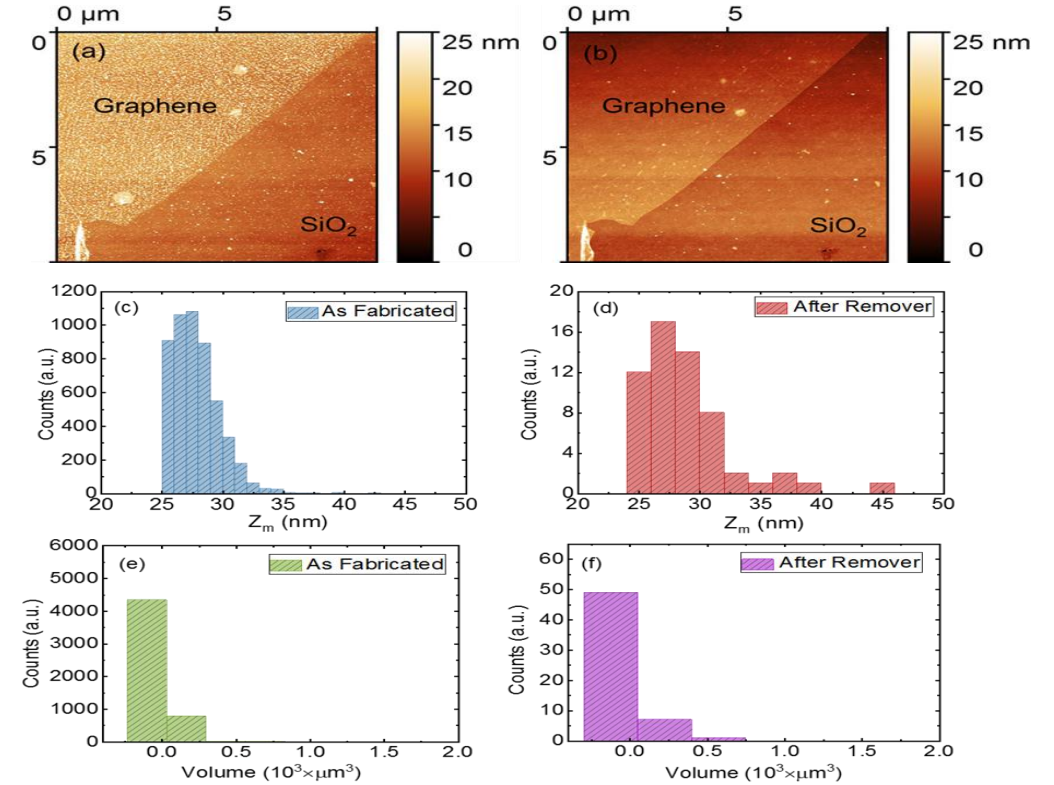
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# Raman and AFM data after device fabrication and cleaning with remover



- Remover consistently improves the properties of graphene even after fabrication without creating any defect in the graphene.



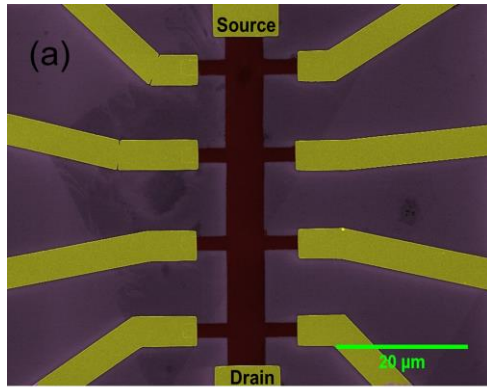
- Height and the volume analysis of the PMMA residues strongly correlates with the Raman results.

Tyagi et al in preparation.

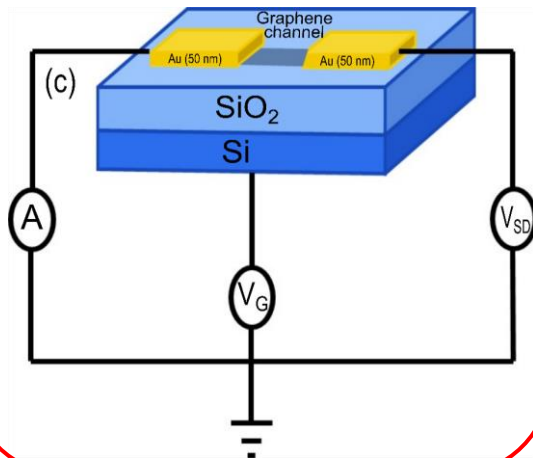
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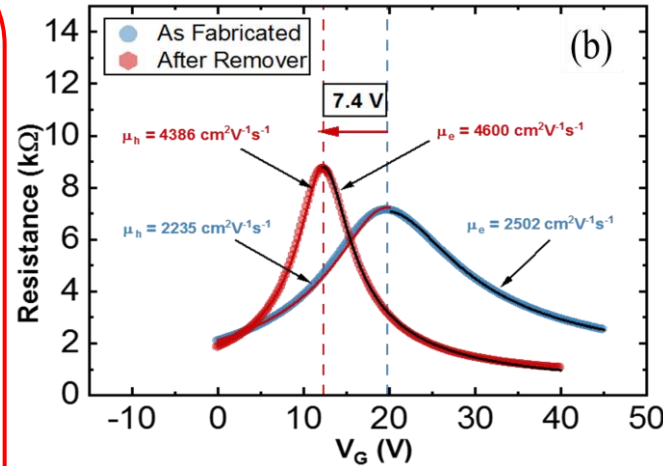
# Mobility calculation of graphene with and without Remover



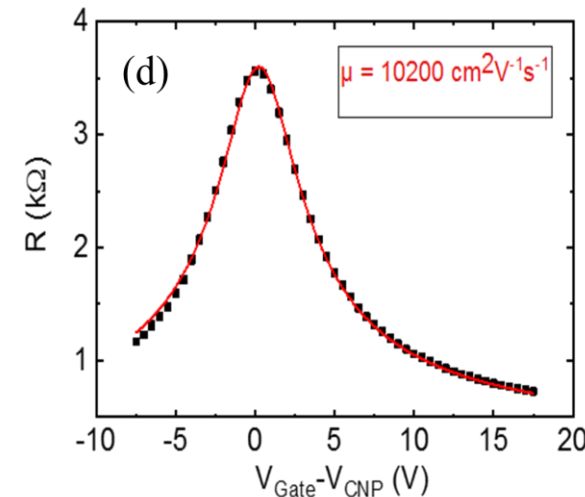
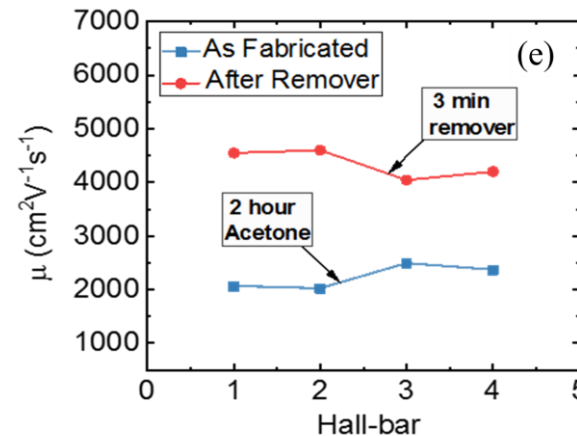
Graphene Hall-bar fabricated using e-beam lithography on Si/SiO<sub>2</sub>.



Schematics of back-gated graphene FET.



- Graphene mobility is nearly doubled after cleaning with remover as the PMMA residues are dissolved which act as external scattering centers for the carriers in graphene.



- By slightly modifying the process recently even we have achieved  $\mu = 10k \text{ cm}^2\text{V}^{-1}\text{s}^{-1}$  which is basically among the highest values till now reported on Si/SiO<sub>2</sub>.

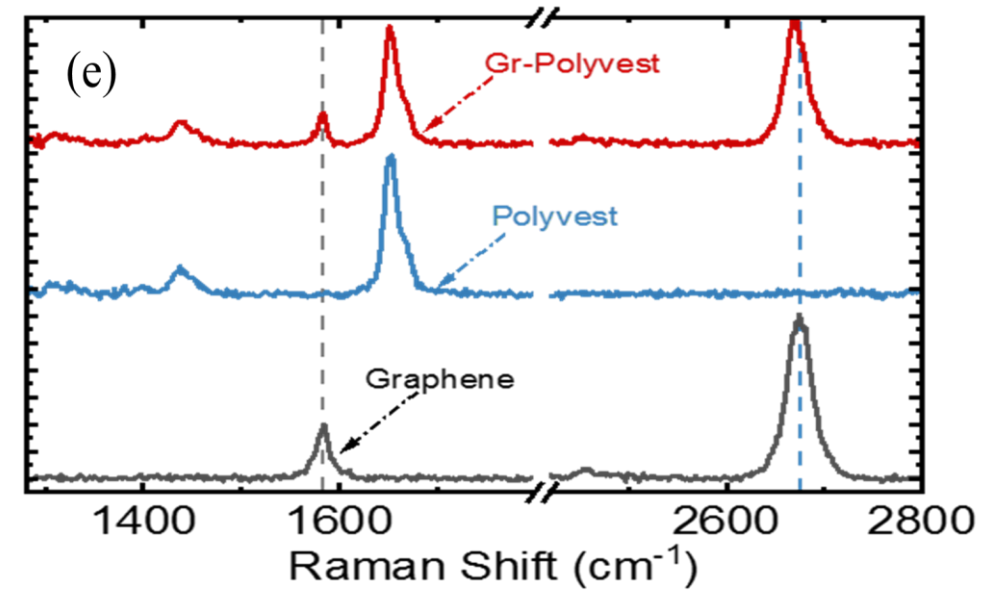
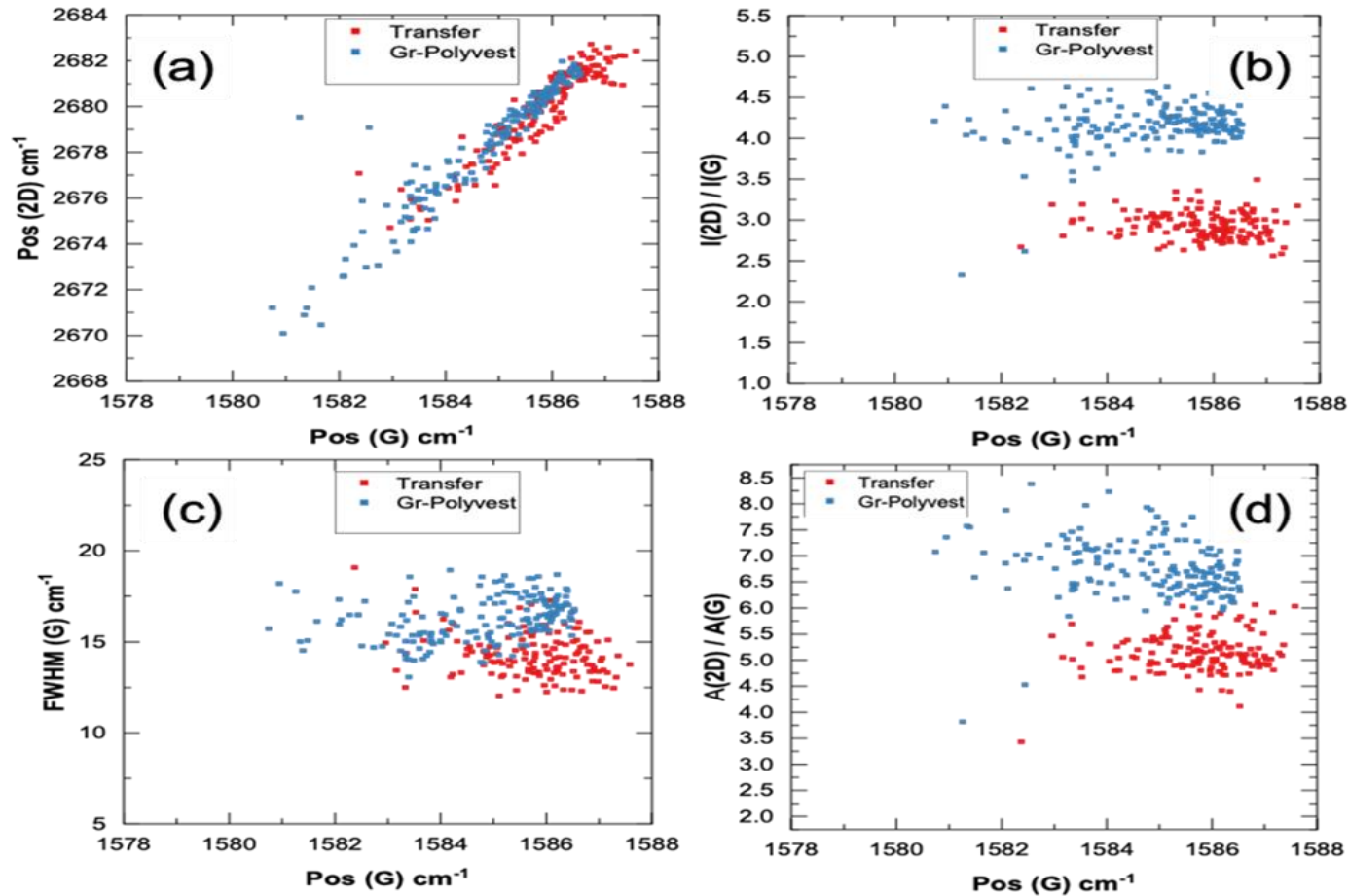
Tyagi et al in preparation.

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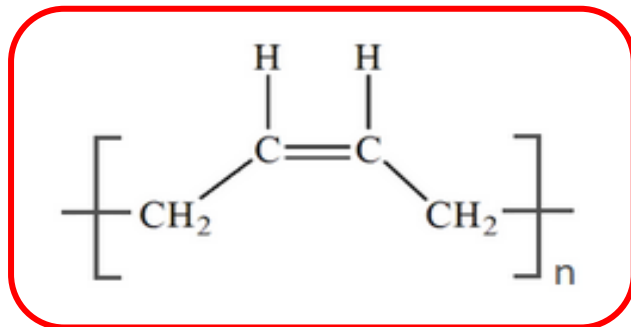
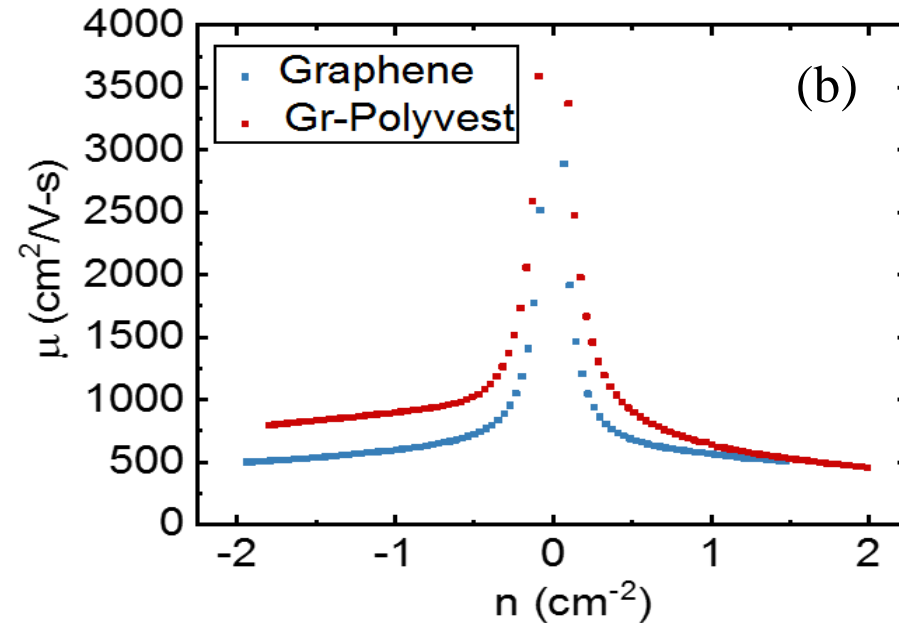
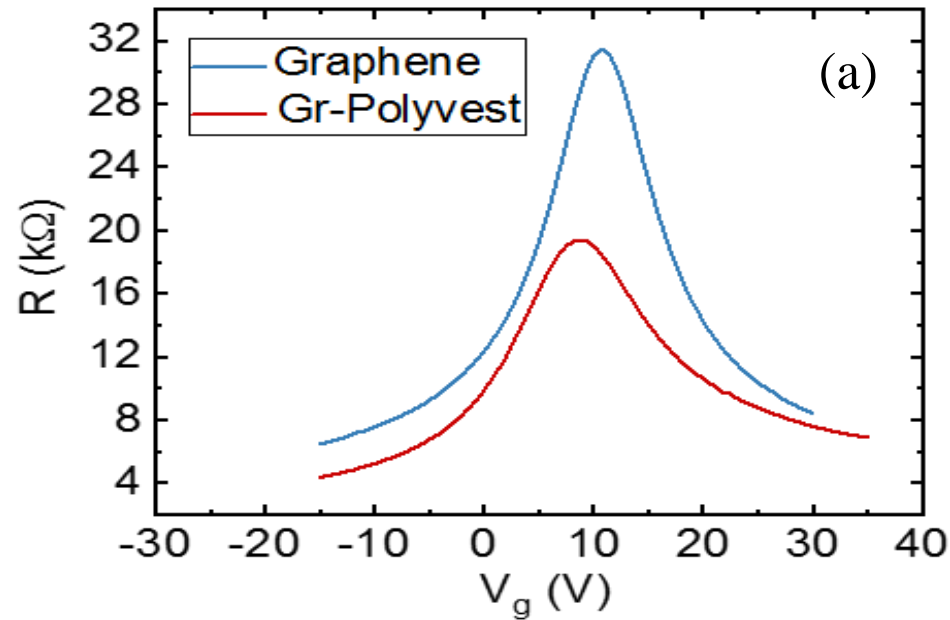
## Project - 2

### Graphene-Polyvest (Polybutadiene): Raman analysis



Raman data indicate doping reduction in p-type doped graphene as  $I(2D)/I(G)$ ,  $A(2D)/A(G)$  and FWHM(G) increase.

## Graphene-Polyvest (Polybutadiene): electrical transport

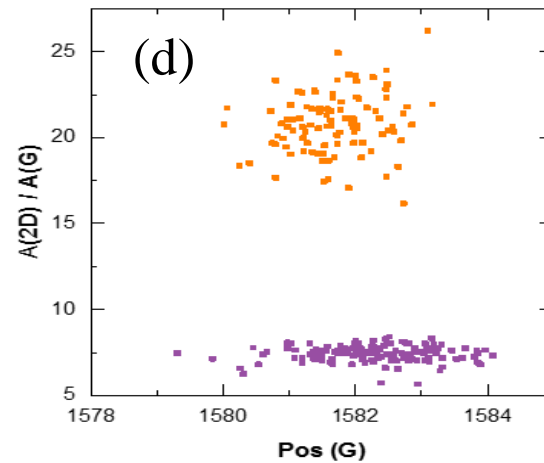
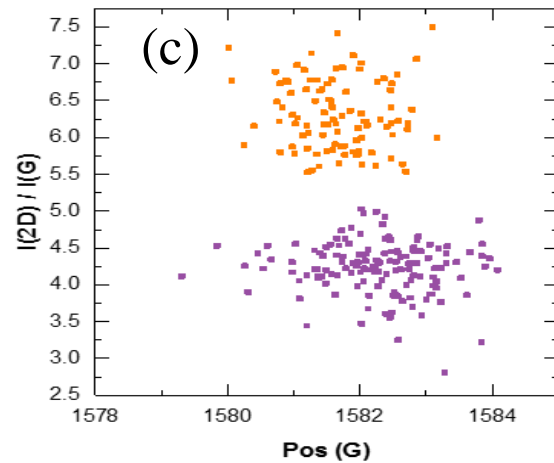
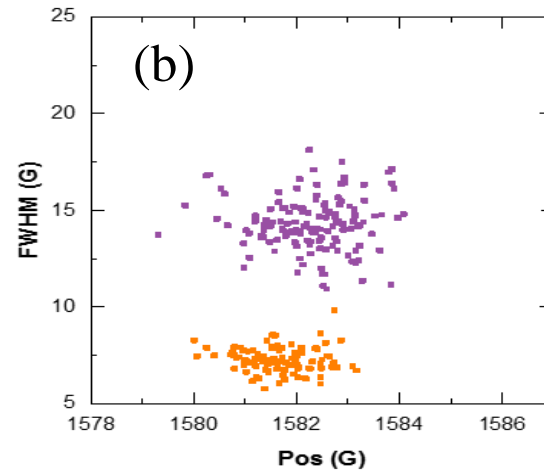
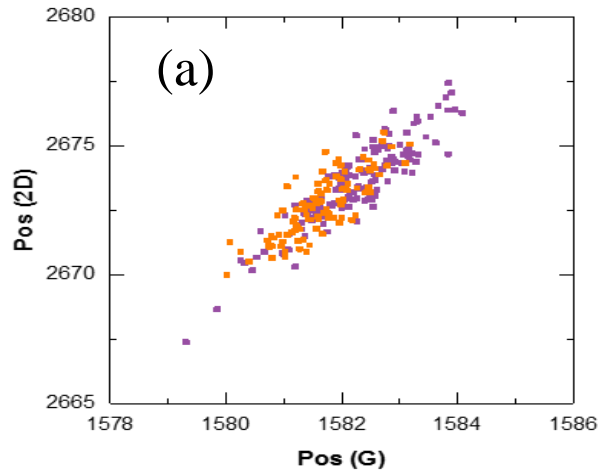


Polyvest  
(Polybutadiene)

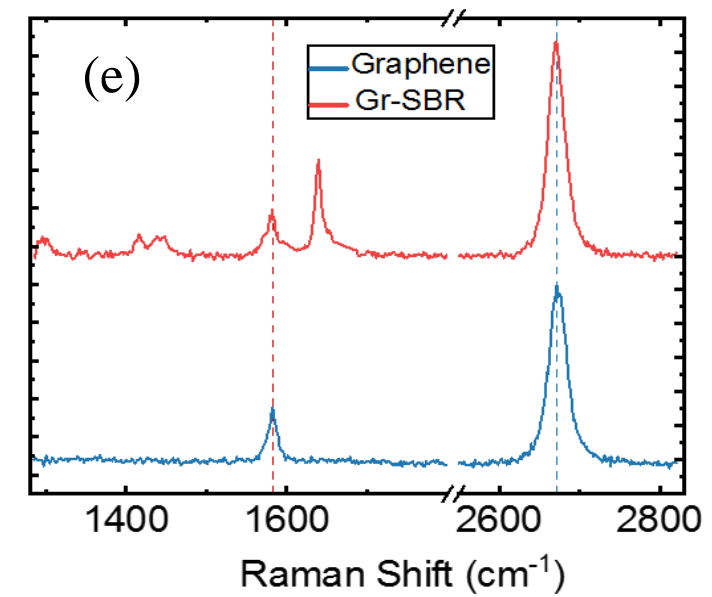
Polyvest has excess electrons that by charge transfer might reduce the p-type doping in graphene towards charge neutrality.



## Graphene-SBR (styrene butadiene): Raman results

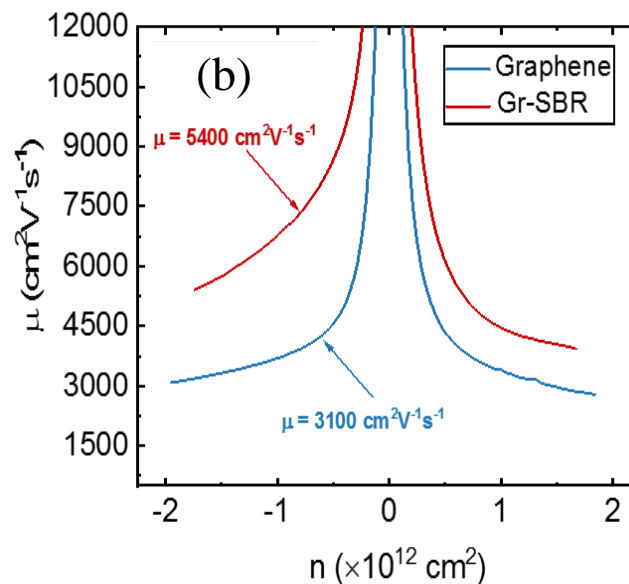
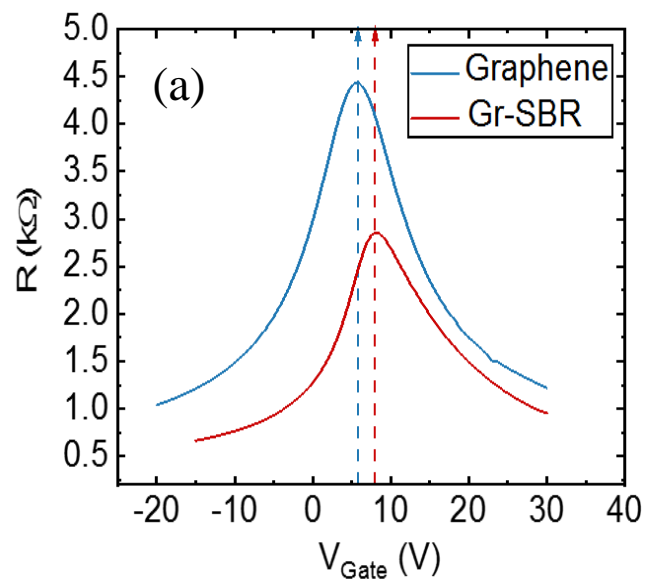


■ Graphene  
■ Gr-SBR

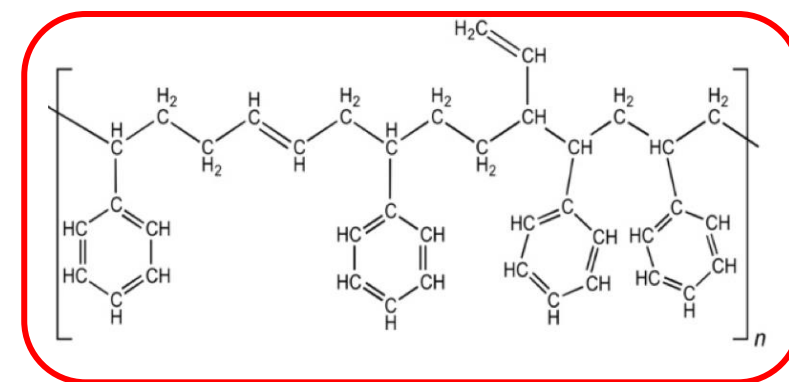


Graphene-SBR Raman data indicate even stronger doping reduction in graphene than when using polyvest.

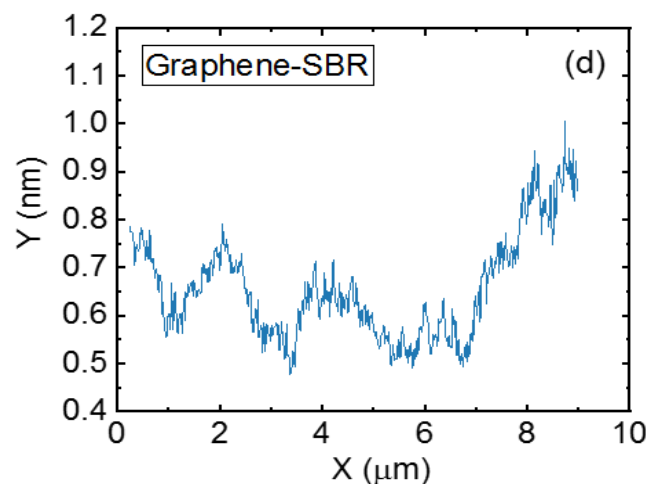
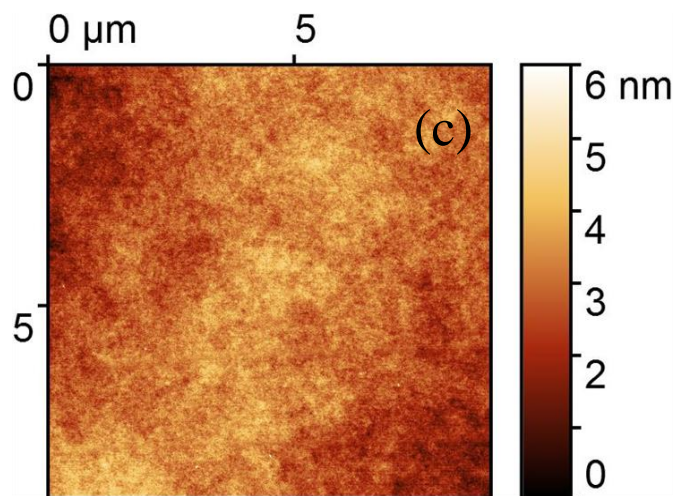
## Graphene-SBR (styrene butadiene): electrical transport and AFM data



Graphene mobility became almost twice after depositing SBR thin film.



SBR (Styrene butadiene)



Graphene-SBR AFM confirms conformal and homogenous SBR coating over graphene with roughness(RMS) of  $< 1 \text{ nm}$ .

# Conclusion and Future Perspective

## Project-1

- An efficient and rapid way of cleaning CVD graphene is developed.
- Electrical and morphological properties are enhanced.
- The clean graphene can be used for different applications i.e., high performance electrical and optical devices, to get high performance heterostructures with other 2D materials etc.

## Project-2

- Change in the properties of graphene by using polymers i.e., Polyvest (polybutadiene) and SBR (styrene butadiene) is investigated.
- These results are the important steps to understand the interaction between graphene and rubbers as a filler material for the graphene tires.
- These two polymers could be the promising candidates as a polymeric dielectric material.
- Effect of pyrroles together with graphene/rubber adducts is in process.

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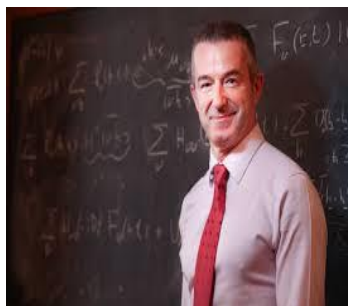


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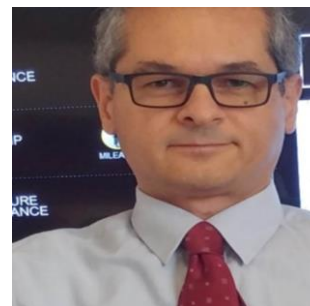


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Prof. Fabio Beltram



Luca Giannini  
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